



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# BTA420-800CT

3Q Hi-Com Triac

4 February 2013

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series CT" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ }^{\circ}\text{C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High junction operating temperature capability
- High voltage capability
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Heating controls
- High power motor control
- High power switching

## 4. Quick reference data

Table 1. Quick reference data

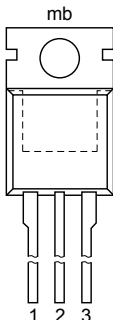
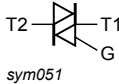
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	200	A
$T_j$	junction temperature		-	-	150	$^{\circ}\text{C}$
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 122\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	20	A



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	35	mA
<b>Dynamic Characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	1250	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 20 A; dV <sub>com</sub> /dt = 10 V/μs; gate open circuit	16	-	-	A/ms

## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p style="text-align: center;"><b>TO-220AB (SOT78)</b></p>	 <p style="text-align: center;"><i>sym051</i></p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BTA420-800CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BTA420-800CT	BTA420-800CT

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 122\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	20	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	200	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	220	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	200	$A^2s$
$di_T/dt$	rate of rise of on-state current	$I_T = 24\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu s$	-	100	$A/\mu s$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}C$
$T_j$	junction temperature		-	150	$^{\circ}C$

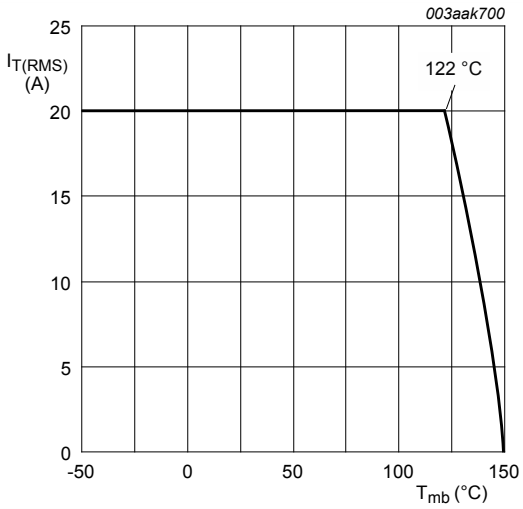
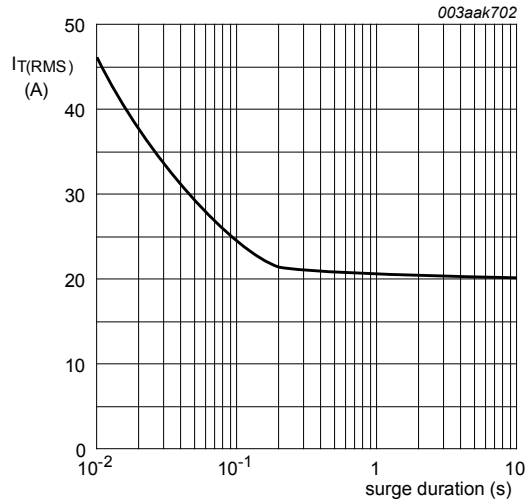
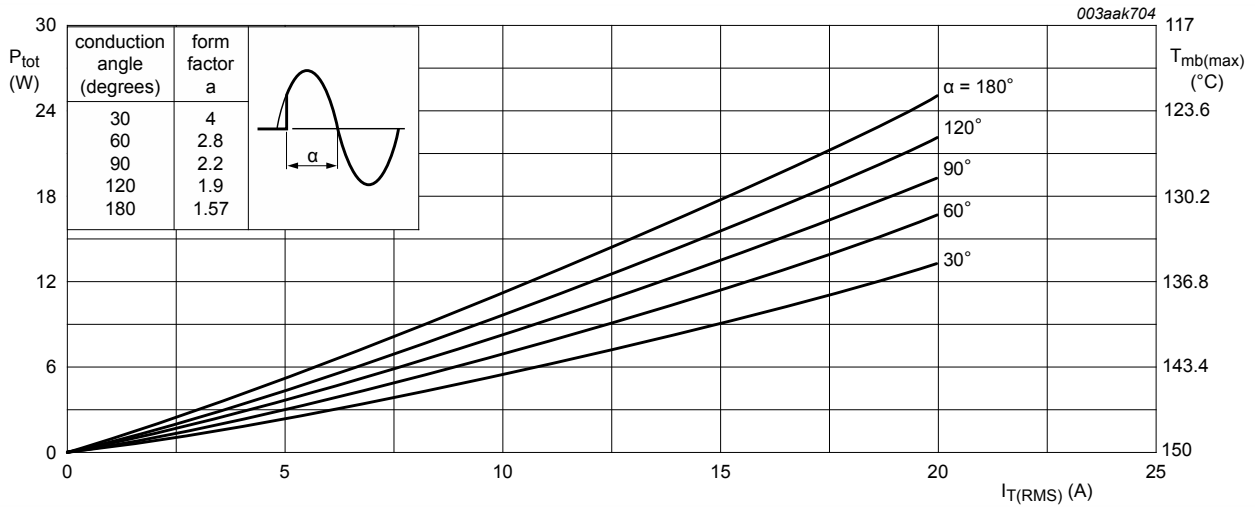


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



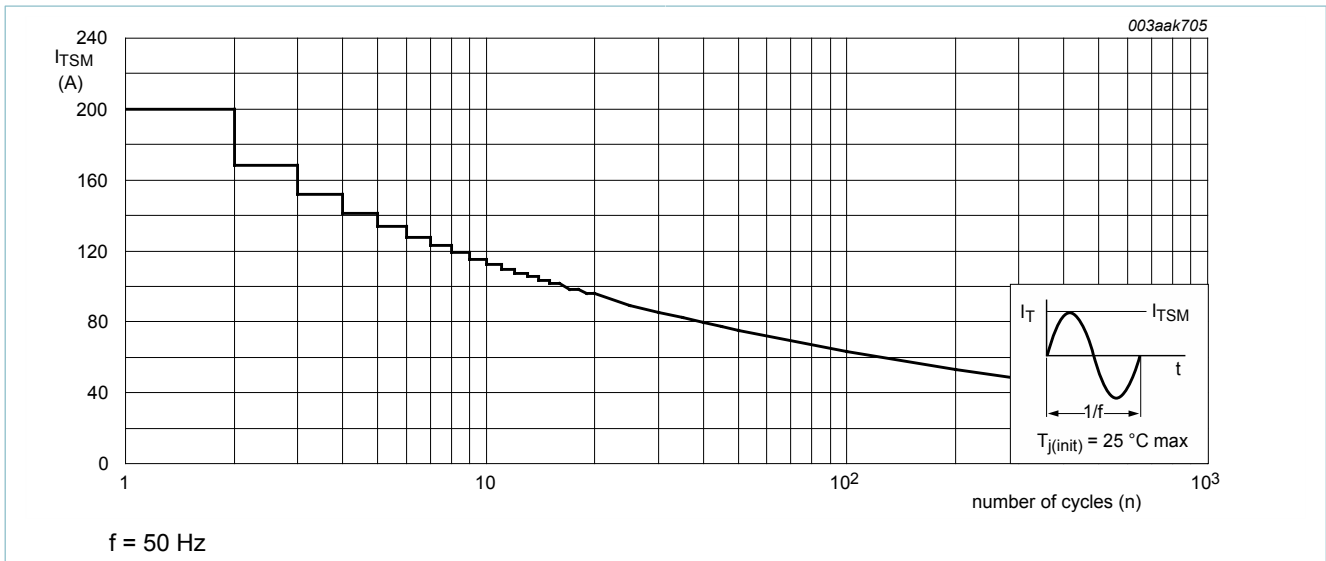
$f = 50$  Hz;  $T_{mb} = 122$  °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

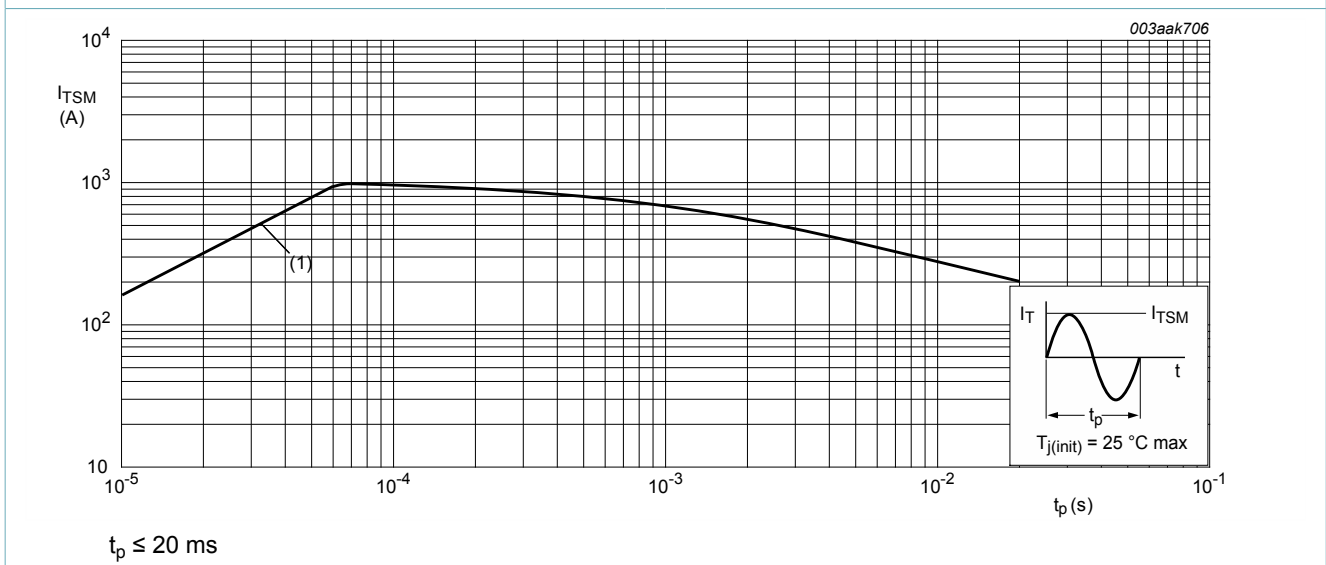


$\alpha$  = conduction angle

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**

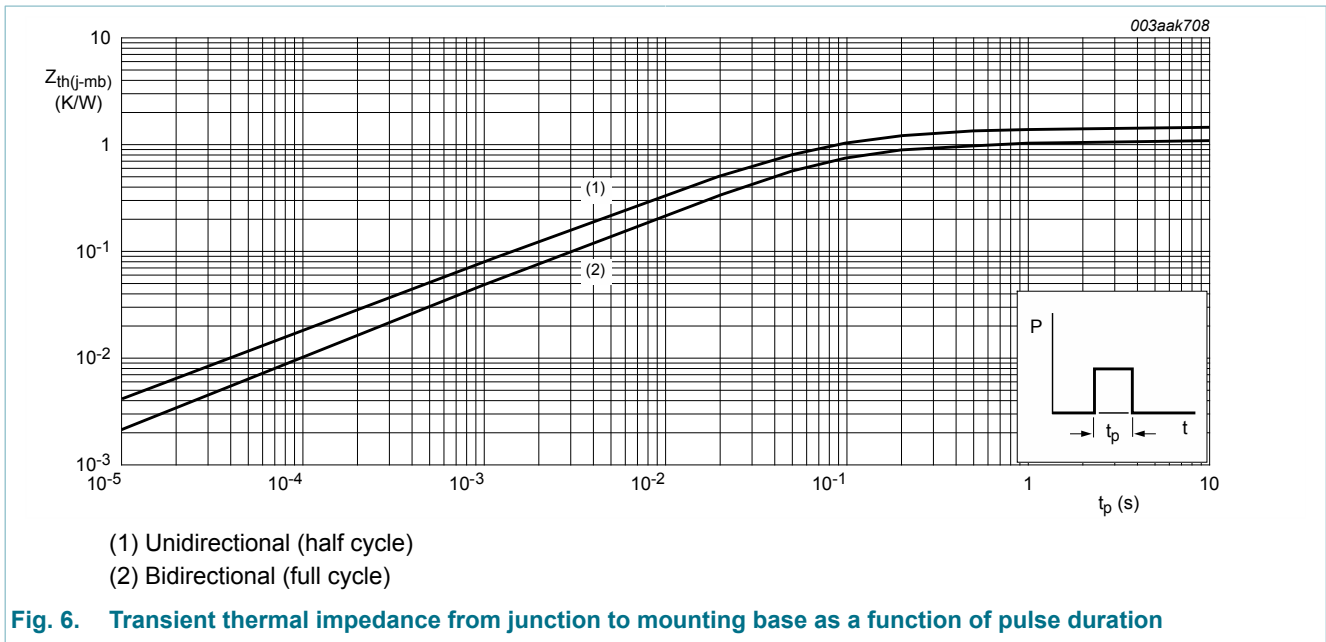


**Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values**

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	1.1	K/W
		half cycle; <a href="#">Fig. 6</a>	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

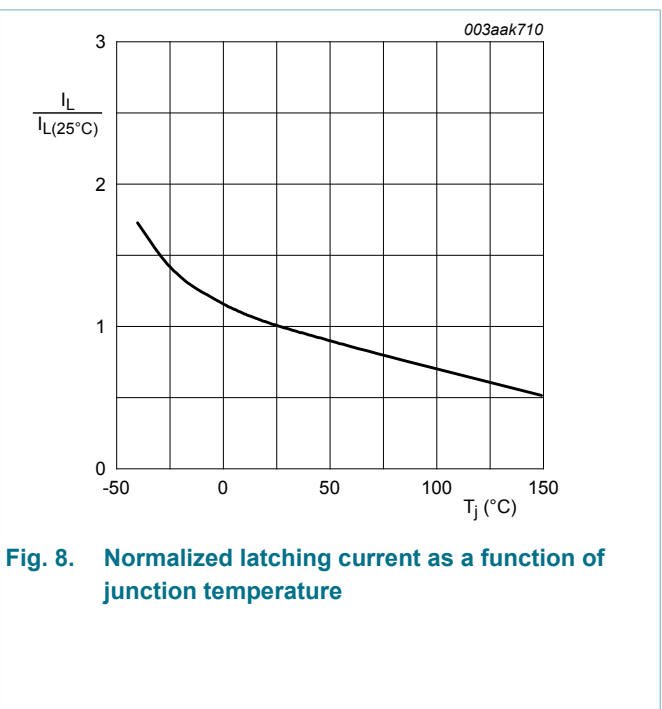
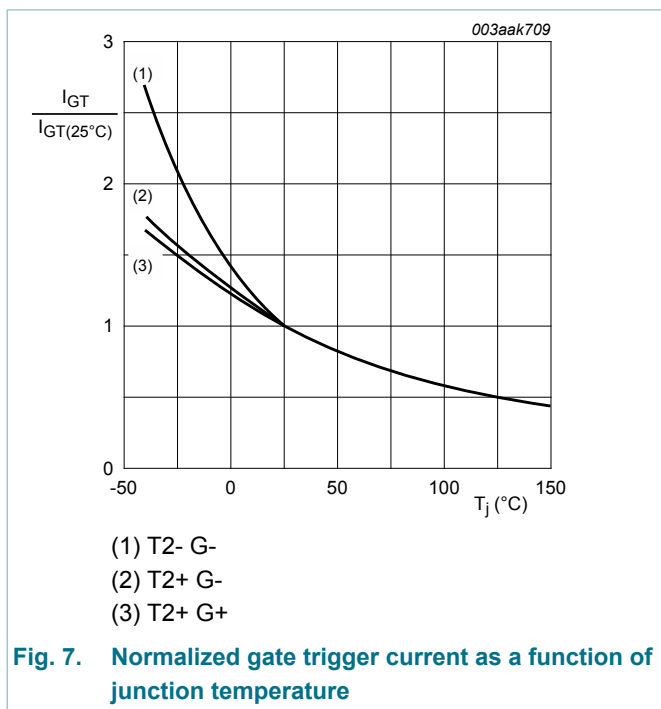


## 10. Characteristics

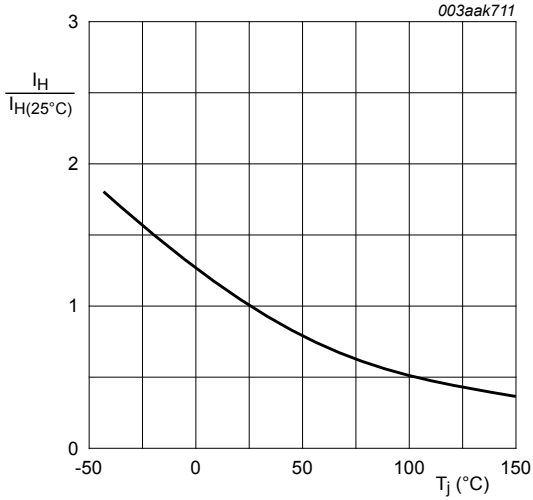
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	-	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	-	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	50	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	80	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	-	40	mA
$V_T$	on-state voltage	$I_T = 24\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	0.7	1	V
		$V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	0.2	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	0.2	1	mA

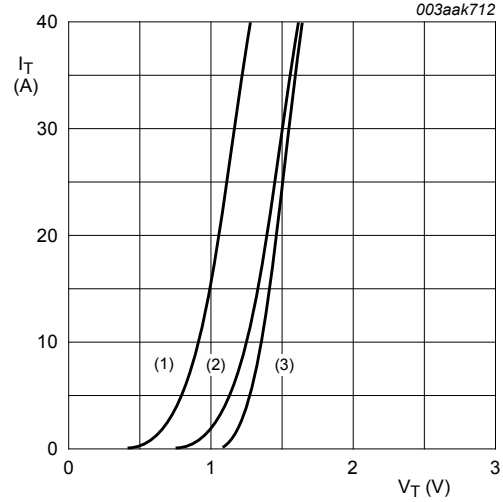
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic Characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	1250	-	-	V/ $\mu\text{s}$
$di_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 20\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	16	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 20\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	38	-	-	A/ms





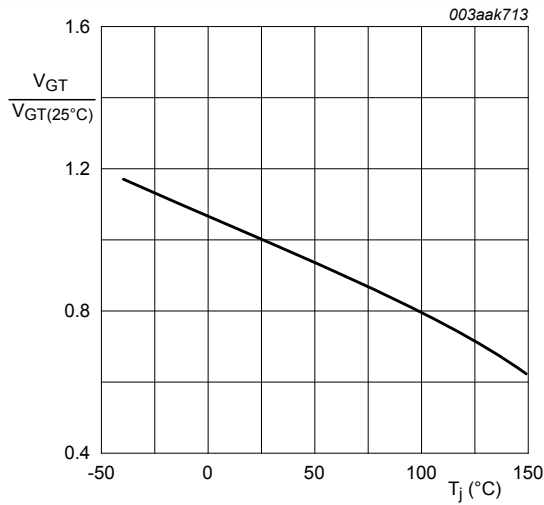


**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.087 \text{ V}; R_s = 0.014 \Omega$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**



**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

### 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

**Fig. 12. Package outline TO-220AB (SOT78)**

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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